

## Schottky Barrier Diode

## FQ1JP10L

**Features**

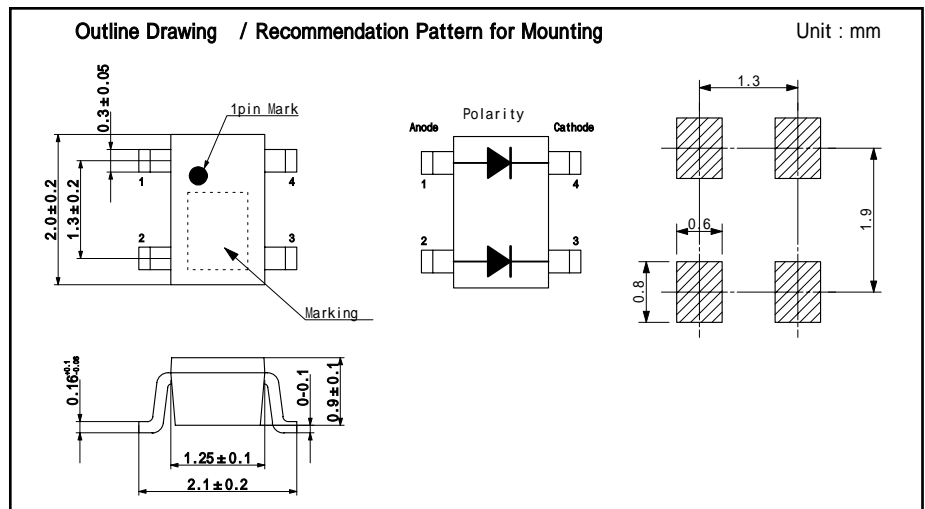
- Four or eight terminals for high density mounting.
- Low VF , Low IR and 100V

**Applications**

- Small size power supplies
- Preventing from reverse current by Wrong setting of a battery

**Structures**

- Marking symbol : [ JP ]
- Weight : 6mg
- Terminal plating : Sn-2Bi
- Conforms to RoHS regulations

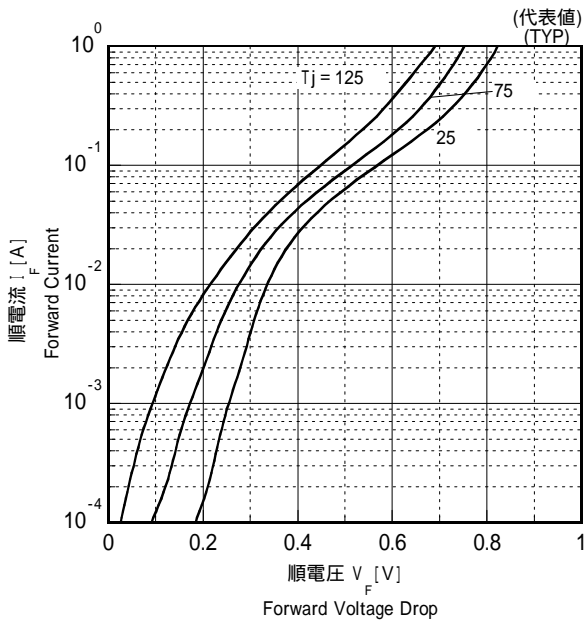
**Absolute Maximum Ratings (Ta=25 )**

Items	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	$V_{RM}$		100	V
Non-Repetitive Peak Reverse Voltage	$V_{RSM}$		105	V
Average Rectified Forward Current	$I_O$	Ta=75 , 50Hz Half sin wave 180 ° R-Load, 2 diodes active , maximum current (100mA per leg)	100	mA
Peak Forward Surge Current	$I_{FSM}$	Tj=25 , 50Hz, Single-phase, Half sin wave, Non-Repetitive	1	A
Operating Junction Temperature	$T_j$		-40 ~ +150	
Storage Temperature	$T_{stg}$		-40 ~ +150	

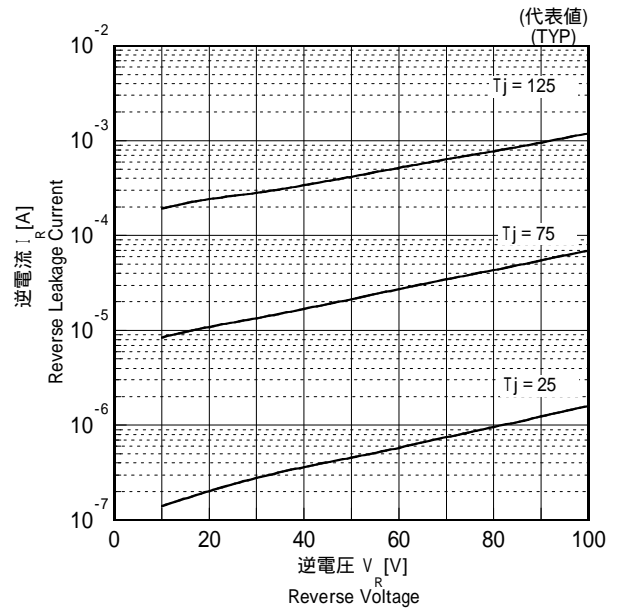
**Electrical Characteristics (Tj=25 )**

Items	Symbol	Conditions	TYP.	MAX.	Unit
Forward Voltage Drop	$V_{F1}$	$I_F=1mA$	0.29	-	V
	$V_{F2}$	$I_F=10mA$	0.39	-	V
	$V_{F3}$	$I_F=100mA$	0.73	0.77	V
Reverse Current	$I_{R1}$	$V_R=40V$	0.15	-	$\mu A$
	$I_{R2}$	$V_R=100V$	-	5.0	$\mu A$
Terminal Capacitance	$C_j$	$V_R=10V, f=1MHz$	8.0	-	pF

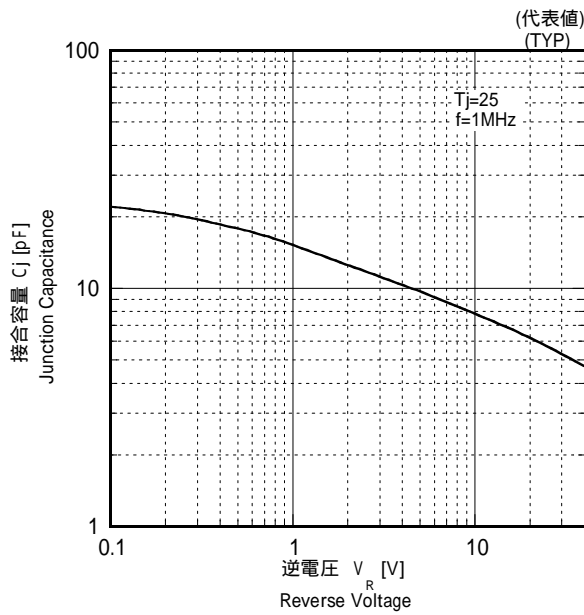
Characteristics Diagrams



FORWARD CHARACTERISTICS



REVERSE CHARACTERISTICS



TYPICAL JUNCTION CAPACITANCE